Title (en)

METHOD FOR FABRICATING A SEMICONDUCTOR PRODUCT WITH A MEMORY AREA AND A LOGIC AREA

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES HALBLEITERPRODUKTS MIT EINEM SPEICHER- UND EINEM LOGIKBEREICH

Title (fr)

PROCEDE DE FABRICATION D'UN PRODUIT SEMICONDUCTEUR COMPRENANT UNE ZONE DE MEMOIRE ET UNE ZONE LOGIQUE

Publication

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Application

**EP 02794526 A 20020730**

Priority

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Abstract (en)

[origin: WO03015161A2] The invention relates to a method for integrating field-effect transistors for memory and logic applications in a semiconductor substrate (22). According to said method, the gate dielectric (2) and a semiconductor layer (4) are firstly deposited, on the whole surface thereof, both in the logic and memory areas (6) and (8). The gate electrodes (12) are first of all formed in the memory area (8) from these layers. The source and drain regions (56) are implanted and the memory area (8) is coated with an insulating material (20) in a planarized manner. Only then are the gate electrodes (21) formed in the logic area from the semiconductor layer (4) and the gate dielectric (2).

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